# 2SK0664 (2SK664)

# Silicon N-channel MOSFET

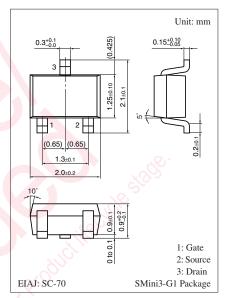
### For switching circuits

#### ■ Features

- High-speed switching
- S-mini type package, allowing downsizing of the sets and automatic insertion through the tape/magazine packing

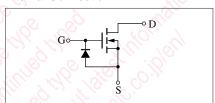
### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V <sub>DSS</sub>	50	V	
Gate-source voltage (Drain open)	$V_{GSO}$	8	V	
Drain current	$I_D$	100	mA	
Peak drain current	$I_{DP}$	200	mA	
Power dissipation	$P_{\mathrm{D}}$	150	mW	
Channel temperature	T <sub>ch</sub>	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



Marking Symbol: 3N

#### Internal Connection



## ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	$V_{ m DSS}$	$I_D = 100 \ \mu A, \ V_{GS} = 0$	50			V
Drain-source cutoff current	$I_{DSS}$	$V_{DS} = 10 \text{ V}, V_{GS} = 0$			10	μΑ
Gate-source cutoff current	$I_{GSS}$	$V_{GS} = 8 \text{ V}, V_{DS} = 0$			50	nA
Gate threshold voltage	V <sub>th</sub>	$I_D = 100 \mu\text{A},  V_{DS} = V_{GS}$	1.5		3.5	V
Forward transfer admittance	Y <sub>fs</sub>	$I_D = 20 \text{ mA}, V_{DS} = 5 \text{ V}, f = 1 \text{ kHz}$	20			mS
Drain-source ON resistance	R <sub>DS(on)</sub>	$I_D = 20 \text{ mA}, V_{GS} = 5 \text{ V}$			50	Ω
Short-circuit forward transfer capacitance (Common source)	C <sub>iss</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$			15	pF
Short-circuit output capacitance (Common source)	C <sub>oss</sub>				5.0	pF
Reverse transfer capacitance (Common source)	C <sub>rss</sub>				1.0	pF
Turn-on time *1, 2	t <sub>on</sub>	$V_{DD} = 5 \text{ V}, V_{GS} = 0 \text{ V} \sim 5 \text{ V}, R_L = 200 \Omega$		10		ns
Turn-off time *1, 2	t <sub>off</sub>	$V_{DD} = 5 \text{ V}, V_{GS} = 5 \text{ V} \sim 0 \text{ V}, R_L = 200 \Omega$		20		ns

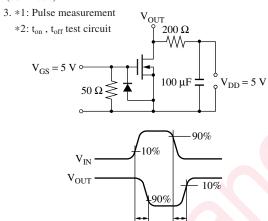
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. Observe precautions for handling. Electrostatic sensitive devices.

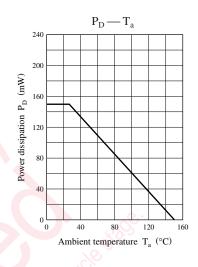
Note) The part number in the parenthesis shows conventional part number.

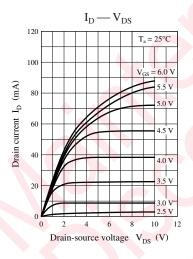
#### ■ Electrical Characteristics (continude)

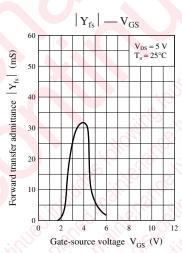
Note) (continude)

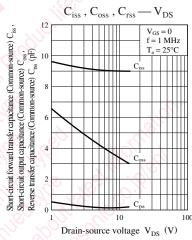


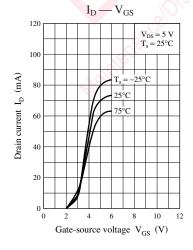
t<sub>off</sub>

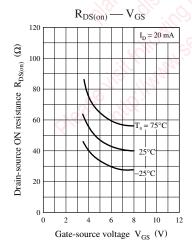


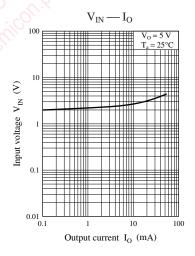












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